

革新的マテリアルのプロセス基盤 カーボンナノチューブでの試行例

- 夢の材料をどう現実に？ $0 \rightarrow 1 \rightarrow 10 \rightarrow 100 \rightarrow 1000\dots$
- マテリアル開発での $0 \rightarrow 1$ vs プロセス開発での $0 \rightarrow 1$
- コスト競争で勝てないから、我が国は品質で勝負...
デバイス性能で勝てる根拠?
プロセス性能で勝てる根拠?

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Carbon Nanomaterials

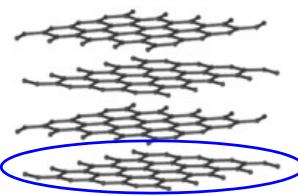
$sp^2 \rightarrow$ graphite



$sp^3 \rightarrow$ diamond



2D: graphene



0D: fullerene 1D: carbon nanotube (CNT)



Dangling-bond less, 2D graphene sheet
realizes stable 0~2D nanomaterials
having both features of
inorganic (strong, stable & conductive)
& organic (soft & light) materials.

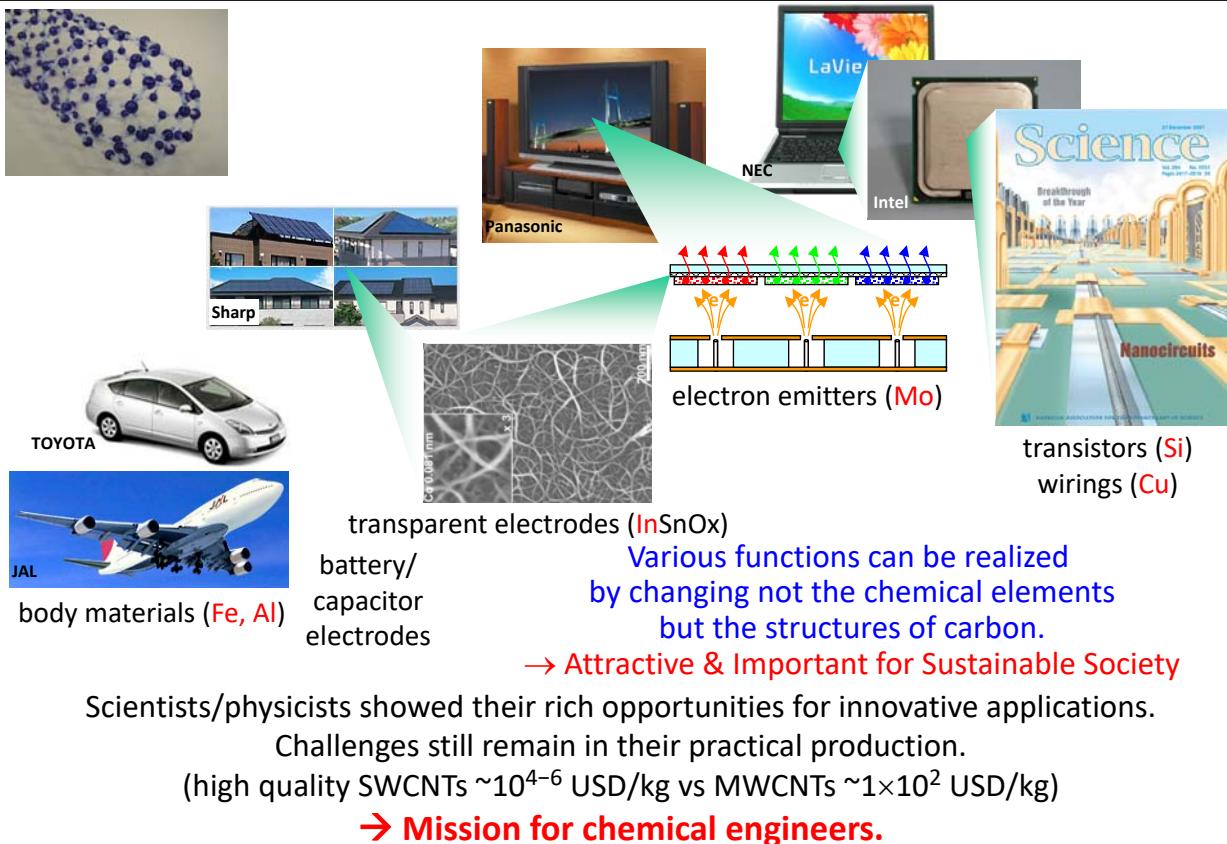
<http://theor.jinr.ru/disorder/nano.html>

SWCNTs: single-walled CNTs

FWCNTs: few-wall CNTs

MWCNTs: multi-wall CNTs

Rich Opportunities and Challenges with CNTs



Various Carbon Nanotubes & Nanofibers

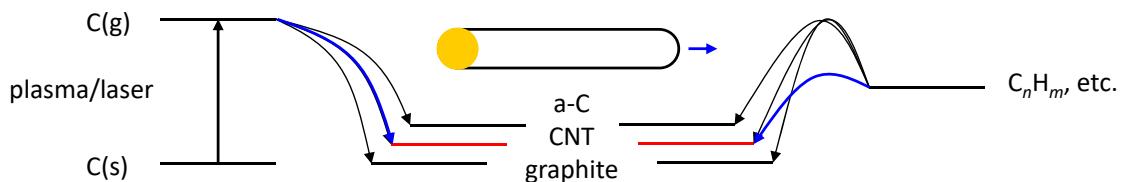
OCSiAl	MEIJO NanoCarbon	CNano	Showa Denko
TUBALL	MEIJO eDIPS	FloTube 9000	VGCF-H
http://ocsial.com/	http://meijo-nano.com/	http://www.marubeni-sys.com/cnt/cnano/	http://www.sdk.co.jp/products/vgcf-h.html
single-wall	single-wall	multi-wall (10–20)	vapor growth
$d = 1.5$ nm	$d = 1, 1.5, 2$ nm	$d = 10\text{--}15$ nm	$d = 1\text{--}10$ nm
$l > 5$ μm		$l = 10$ μm	
C > 85 wt%	C > 50, 90, 99 wt%	C = 95–97.5 wt%	
CNT > 75 wt%			
9 USD/g (100 g)	1600–150 USD/g (1 g)	0.1 USD/g ? (>kg)	
○	○ ○ ○		
<i>A kind of “inorganic polymer made of only carbon”</i>			

Production Methods of CNTs

Physical Vapor Deposition

Carbon vapor is formed by heating solid carbon source by arc/laser.

Solid carbon including tubes is formed during cooling.



Chemical Vapor Deposition

Carbon-containing gas molecules are decomposed through chemical reactions, yielding solid carbon including tubes.

High temperature (& solid C-source)
 \Leftrightarrow High crystallinity

Low temperature & gas C-source
 \Leftrightarrow Large production scale

How to realize small catalyst particles (Fe, Co, Ni, etc.) at high reaction temperatures is an important key to establish production of thin CNTs.

In Situ Observation of CNT Growth from a Catalyst

NANO LETTERS
 2008
 Vol. 8, No. 7
 2082-2086

Atomic-Scale In-situ Observation of Carbon Nanotube Growth from Solid State Iron Carbide Nanoparticles

by environmental TEM, e-TEM

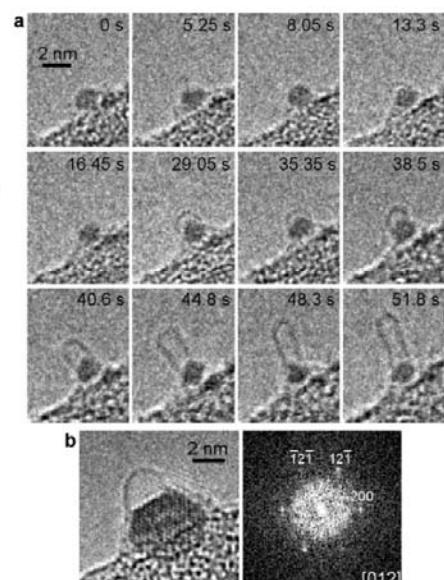
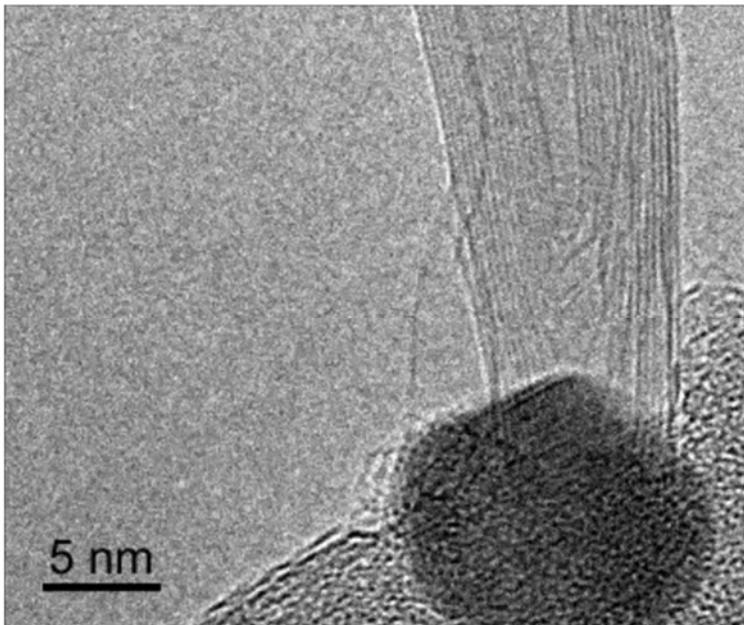
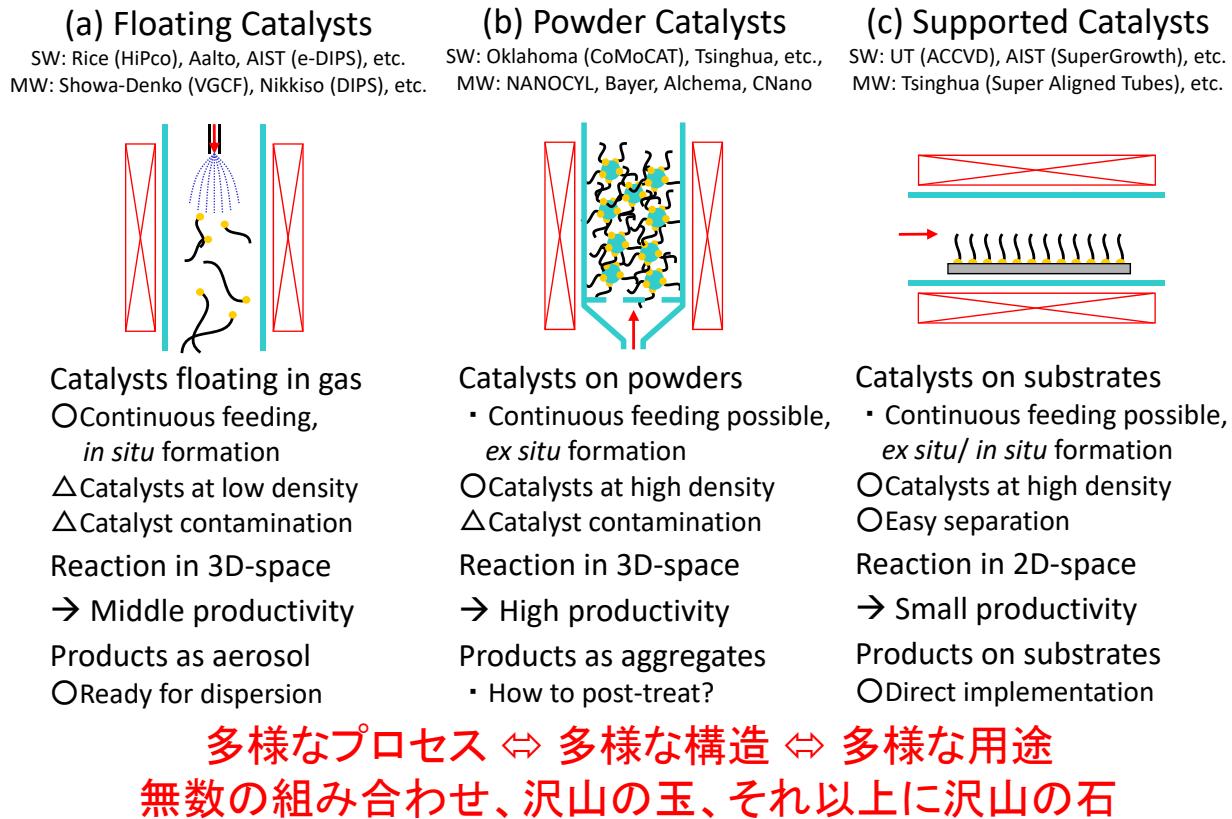


Figure 1. Nucleation and growth process of a SWNT from a NPC on a substrate. (a) Structural fluctuation of both carbon caps and a NPC is observed. The recording time is shown in images. (b) A snapshot of a NPC with a carbon dome. The NPC exhibits the lattice image and the corresponding extra diffraction in the Fourier transform. The NPC can be identified as Fe-carbide (cementite, Fe_3C) viewed along the [012] direction.

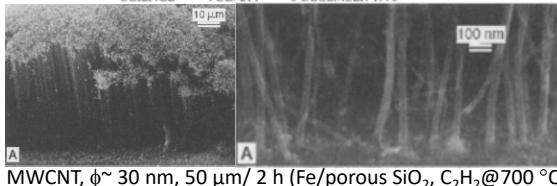
Various CVD Processes



Vertically-Aligned Forests: MWCNTs → SWCNTs^{8/23}

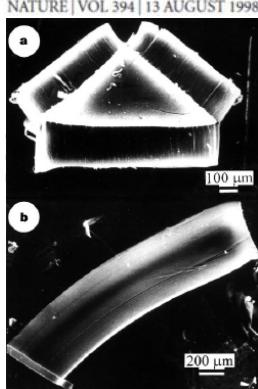
Pioneering Work on MWCNTs Large-Scale Synthesis of Aligned Carbon Nanotubes

W. Z. Li, S. S. Xie,* L. X. Qian, B. H. Chang, B. S. Zou,
W. Y. Zhou, R. A. Zhao, G. Wang
SCIENCE • VOL. 274 • 6 DECEMBER 1996



MWCNT, $\phi \sim 30$ nm, $50 \mu\text{m}$ / 2 h (Fe/porous SiO₂, C₂H₂@700 °C)

Very long carbon nanotubes
NATURE | VOL 394 | 13 AUGUST 1998

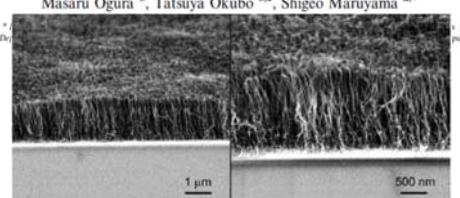


MWCNT, $\phi \sim 30$ nm, 2 mm / 48 h MWCNT, $\phi \sim 16$ nm, 30–240 μm / 5–60 min
(Fe/porous-SiO₂, C₂H₂@600 °C) (Fe/porous-SiO₂, C₂H₄@700 °C)

Alcohol CVD of VA-SWCNTs

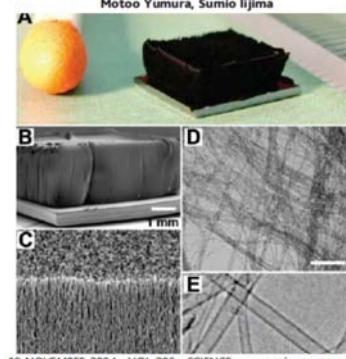
Growth of vertically aligned single-walled carbon nanotube films on quartz substrates and their optical anisotropy

Yoichi Mizutani,^a Shigeru Chiba,^a Toshiaki Miyazaki,^a Minghui Hu,^b Masaru Ogura,^b Tatsuya Okubo,^b Shigeo Maruyama^{a,*}



SuperGrowth of VA-SWCNTs Water-Assisted Highly Efficient Synthesis of Impurity-Free Single-Walled Carbon Nanotubes

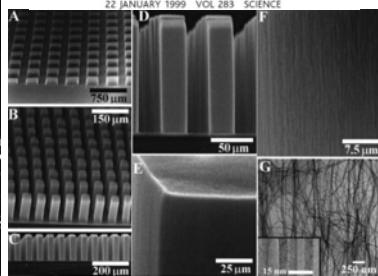
Kenji Hata,^{a,*†} Don N. Futaba,^a Kohhei Mizuno, Tatsunori Namai,
Motoo Yumura, Sumio Iijima



19 NOVEMBER 2004 VOL 306 SCIENCE www.sciencemag.org

Self-Oriented Regular Arrays of Carbon Nanotubes and Their Field Emission Properties

Shoushan Fan, Michael G. Chapline, Nathan R. Franklin,
Thomas W. Tombler, Alan M. Cassell, Hongjie Dai^{*}
22 JANUARY 1999 VOL 283 SCIENCE



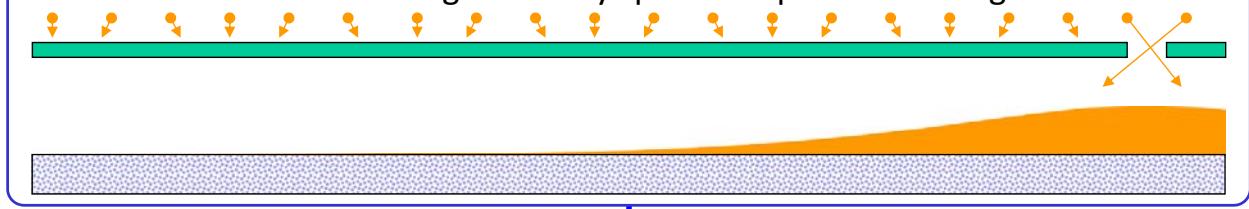
MWCNT, $\phi \sim 30$ nm, 2 mm / 48 h MWCNT, $\phi \sim 16$ nm, 30–240 μm / 5–60 min
(Fe/porous-SiO₂, C₂H₂@600 °C) (Fe/porous-SiO₂, C₂H₄@700 °C)

触媒の効果的な探索・最適化

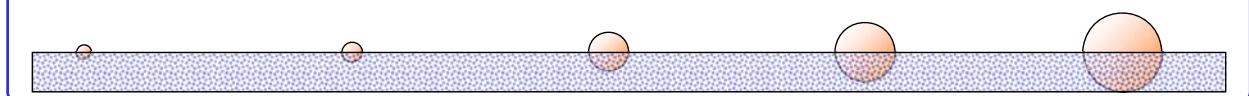
9/23

SN, et al., ASS 225, 372 (2004), APL 86, 173106 (2005).

Controlled thickness gradient by sputter-deposition through a mask



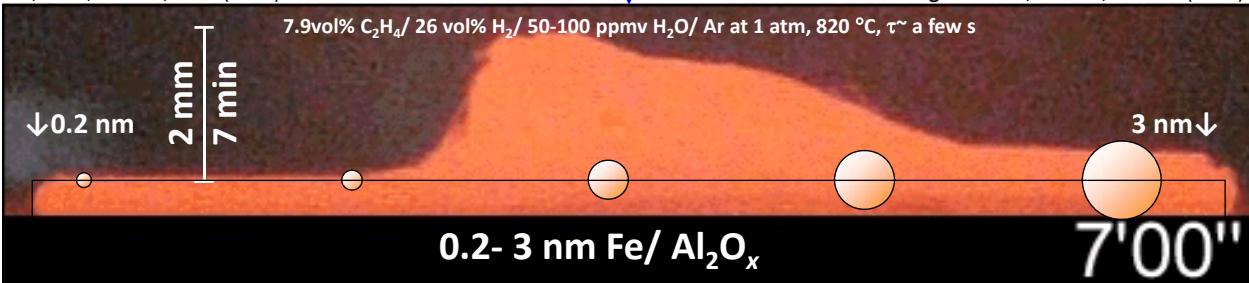
Spontaneous formation of a series of particles at CVD temperatures



SN, et al., JJAP 46, L399 (2007).

K. Hasegawa & SN, JJAP 49, 085104 (2010).

7.9vol% C₂H₄/ 26 vol% H₂/ 50-100 ppmv H₂O/ Ar at 1 atm, 820 °C, τ~ a few s

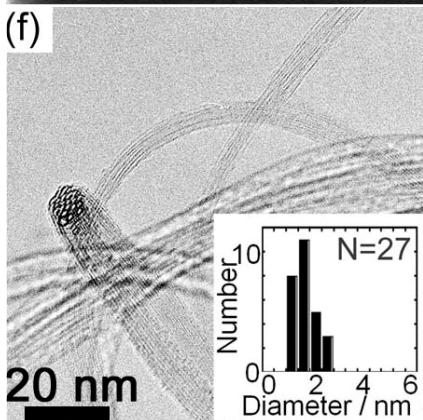
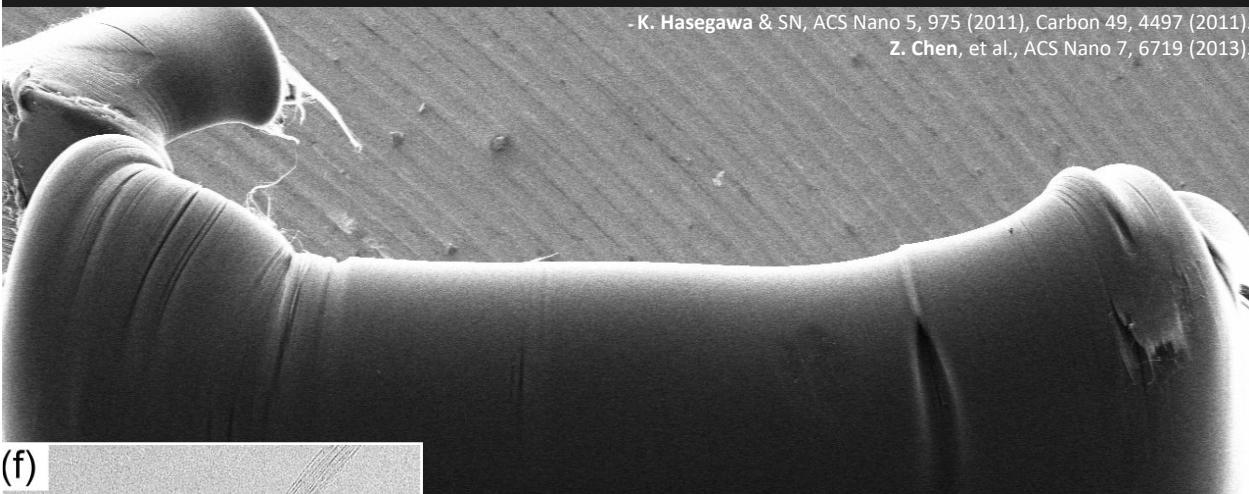


CNTs grow quickly. Extensive trial-error & activity/lifetime in one experiment.

SWCNTs Grown on Flat Substrates

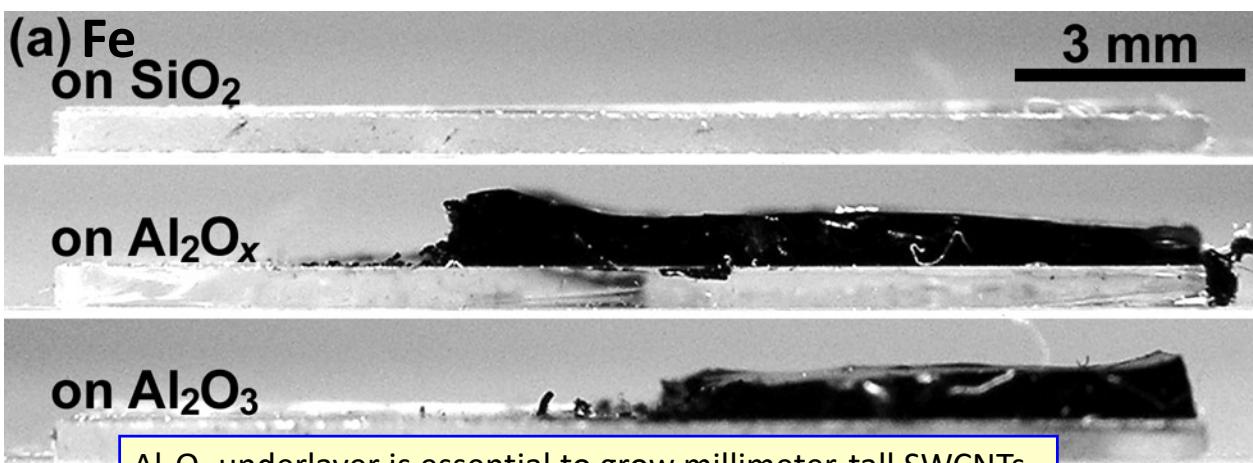
10/23

- K. Hasegawa & SN, ACS Nano 5, 975 (2011), Carbon 49, 4497 (2011).
Z. Chen, et al., ACS Nano 7, 6719 (2013).



反応添加剤・触媒担体

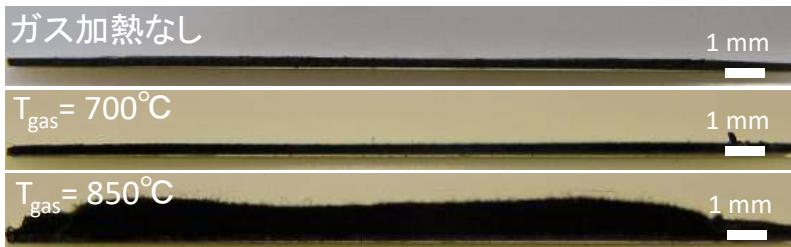
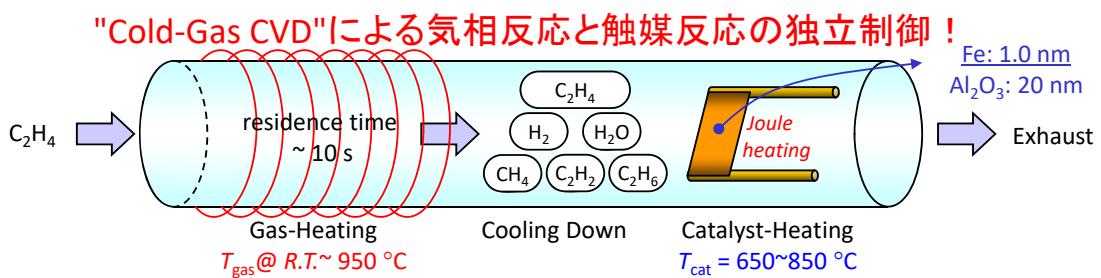
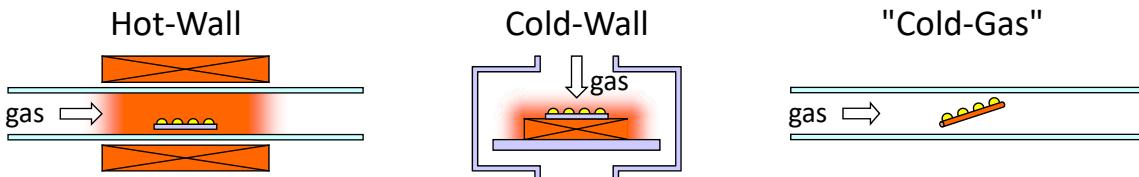
SN, et al., JJAP 46, L399 (2007). K. Hasegawa, et al., JNN 8, 6123 (2008).



炭素原料 vs 反応前駆体

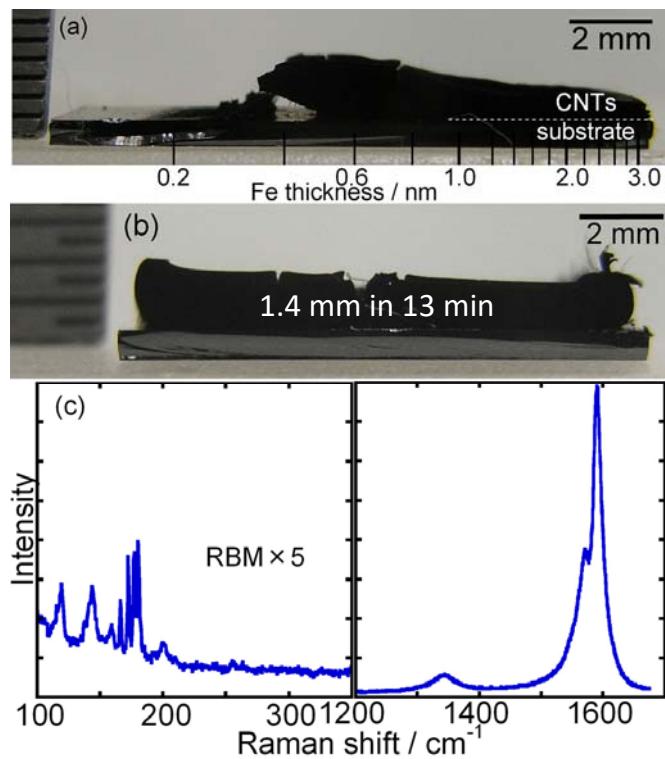
R. Ito, et al., MRS Spring Meeting (2008).

H. Sugime & SN, Carbon 50, 2953 (2012).



C_2H_4 や C_2H_5OH から熱分解で生成する C_2H_2 が前駆体！
 C_2H_2 を直接供給すると、ガスの加熱は不要

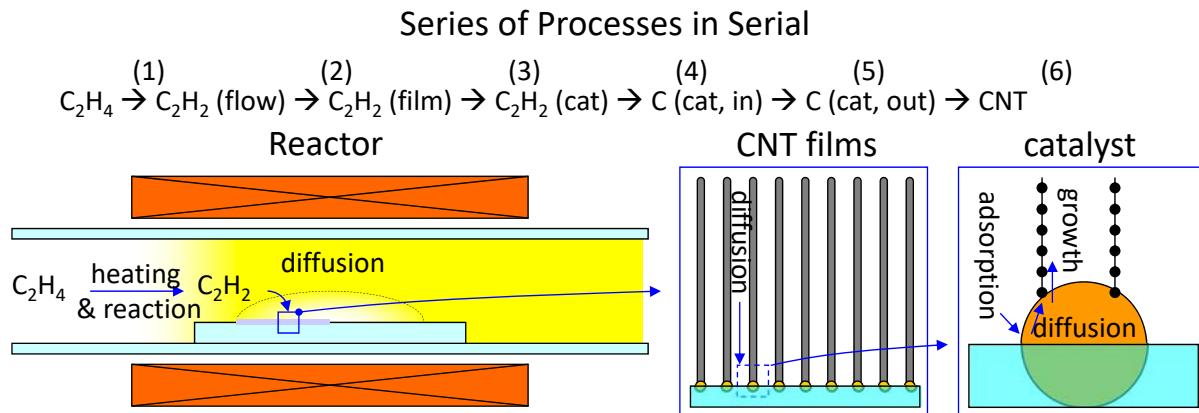
シンプル合成 : C₂H₂/Ar



K. Hasegawa & SN,
ACS Nano 5, 975 (2011).

SWCNTs actually grow tall rapidly without additives.

What Is Occurring in the Reactor?



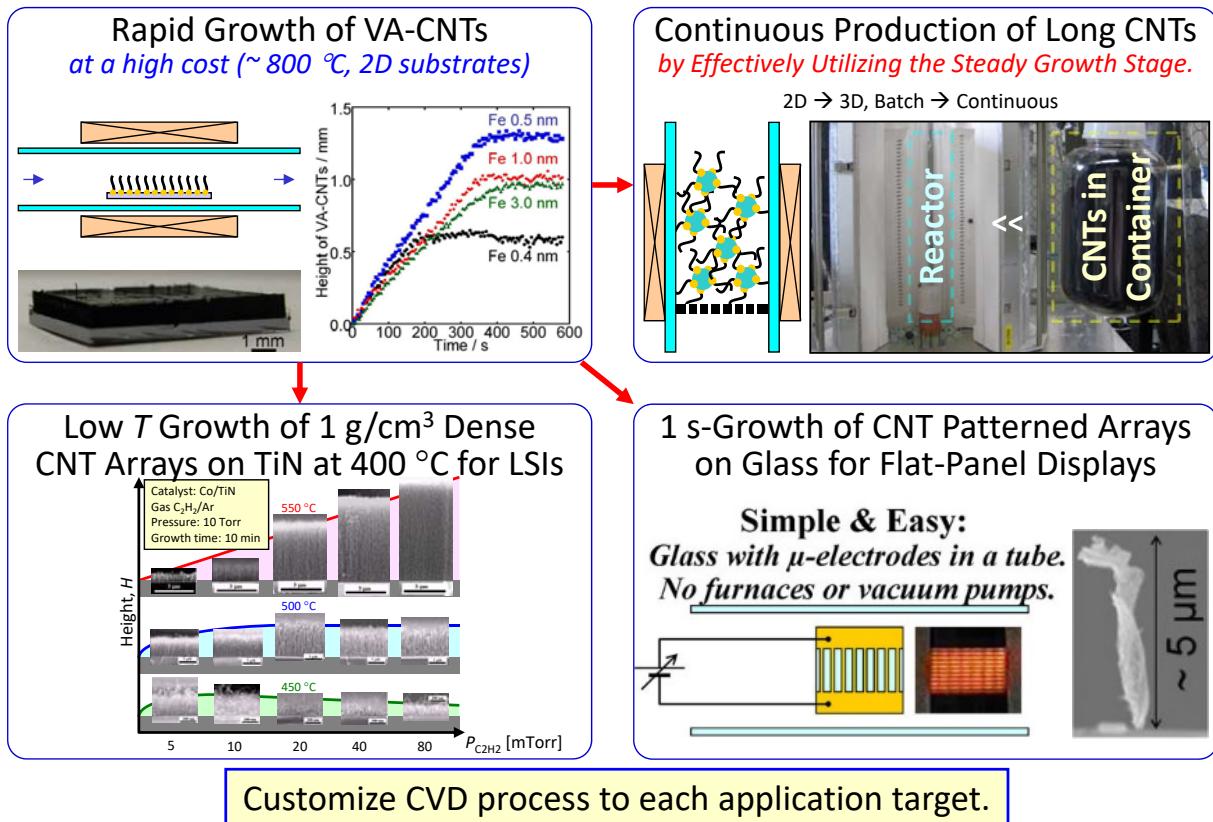
Rate Determining Steps

Serial: Slowest one governs the whole. Parallel: Fastest one governs the whole.



Identify the rate determining step → Efficiently control & newly design CVD

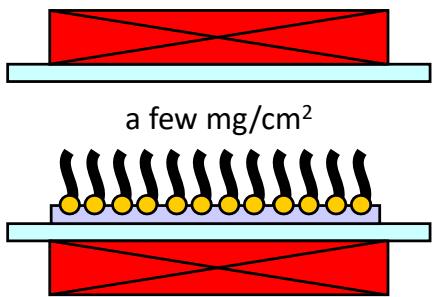
Why CNTs Grow? → How to Grow CNTs? (Previous)



Long CNTs from On-Substrate to Fluidized-Bed

from Semiconductor Process

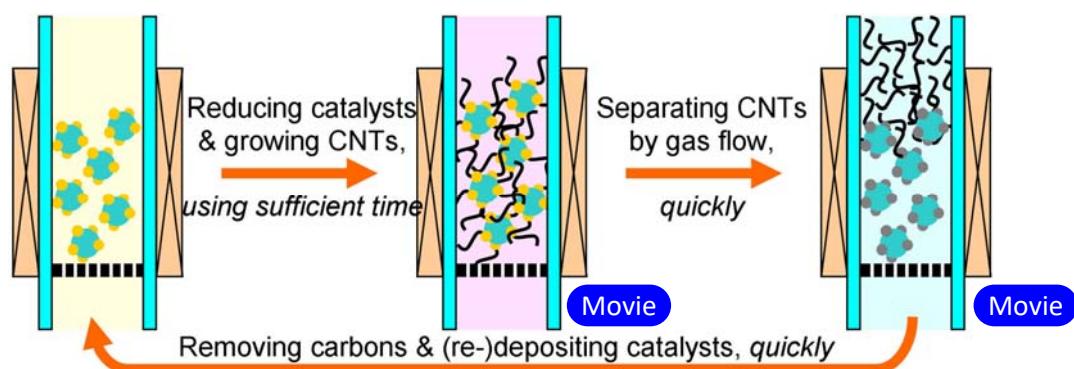
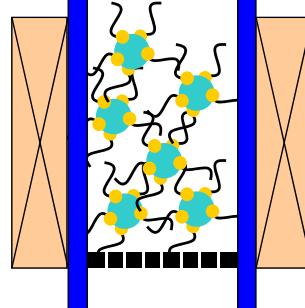
VA-CNTs on 2D substrates

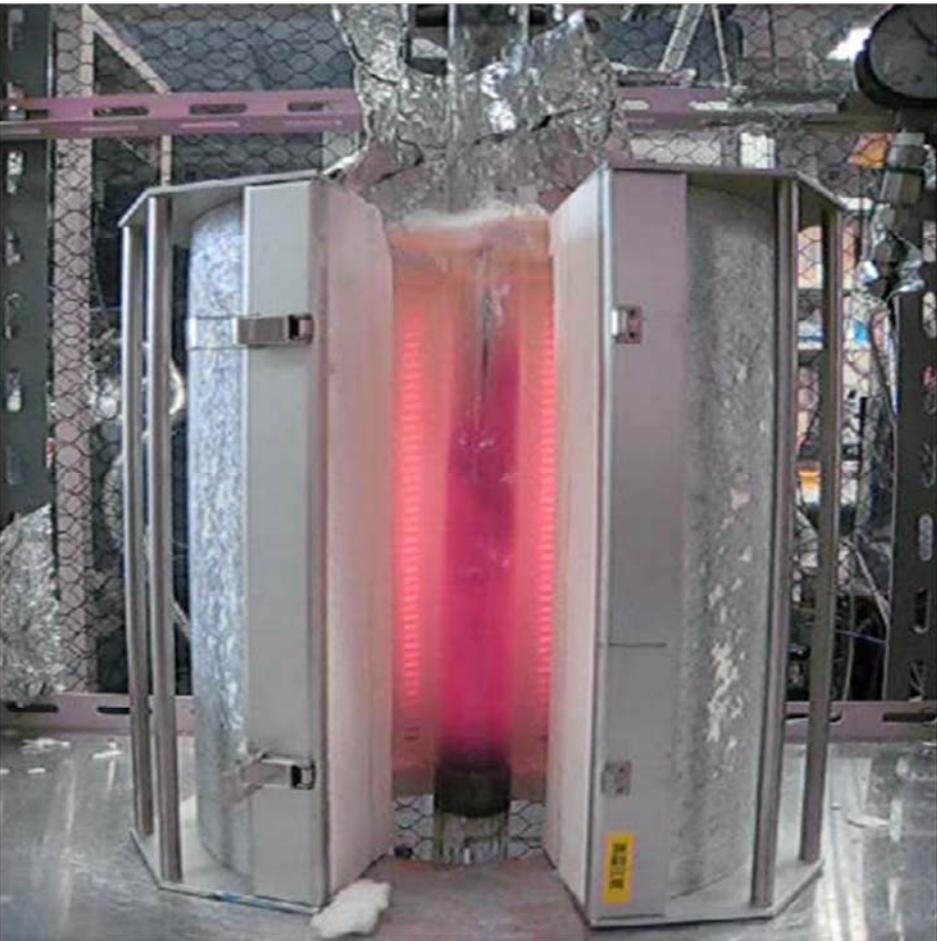


surface area
~ 1,000x
continuous process

to Chemical Process

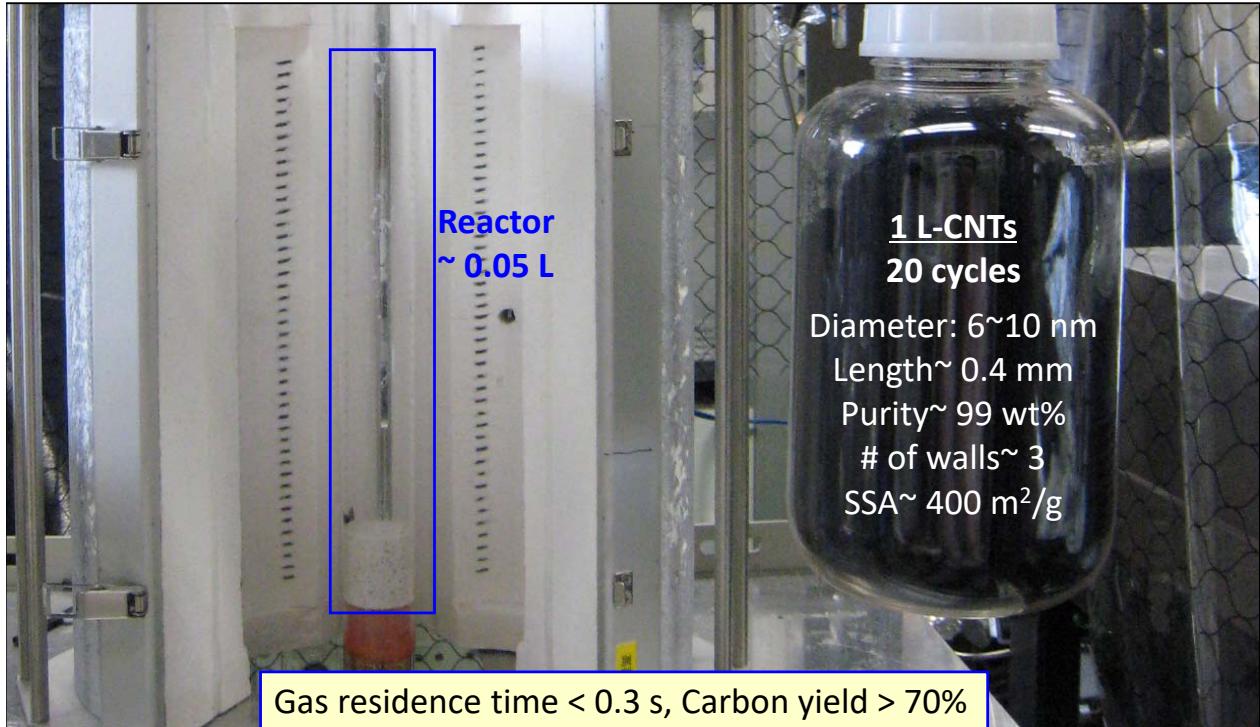
VA-CNTs on beads stuck in 3D





Small Reactor & Big Container

D.Y. Kim, et al., Carbon 49, 1972 (2011).



Si基板での実験と解析 → 速度情報 → プロセス設計(大学院の演習) → ほぼ設計通りに

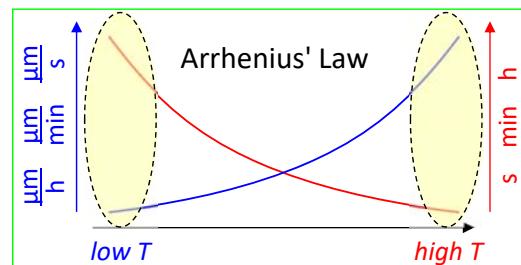
How to Grow CNTs on Display Glass?

(a) Low temperature growth

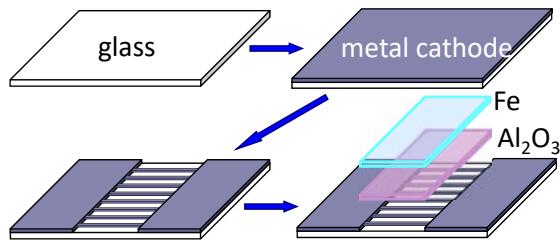
Glass-tolerable temperature
Impractical process time

(b) High temperature growth

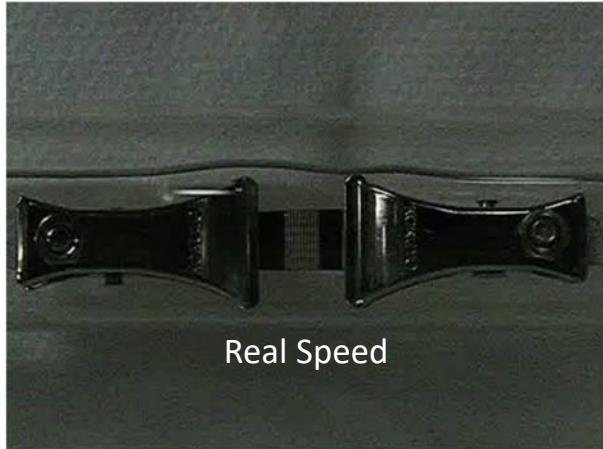
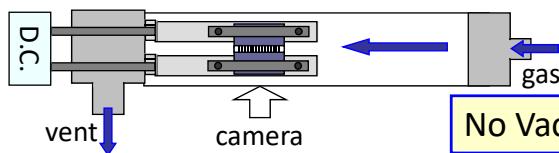
Growth rate $> \mu\text{m/s}$
Glass-tolerable process time
"Hot & instant" is another answer!



Sample preparation



CVD by pulse electrical heating



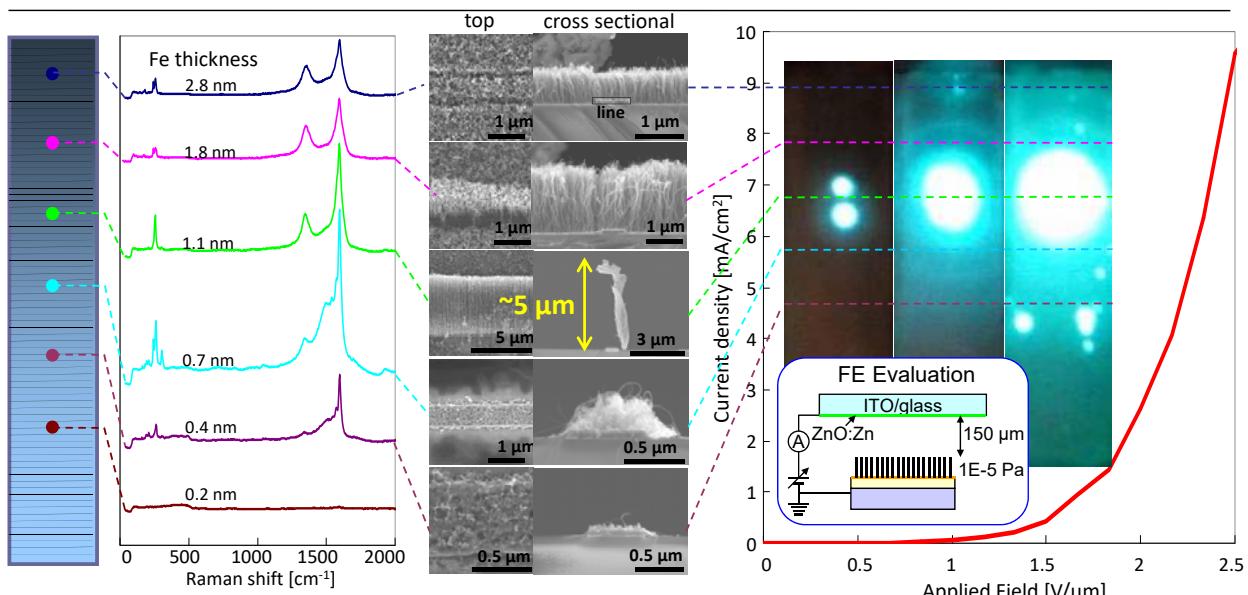
Real Speed

No Vacuum Pump, No Heater! Instant & Easy!

1-s-Fabrication of CNT Emitter Library

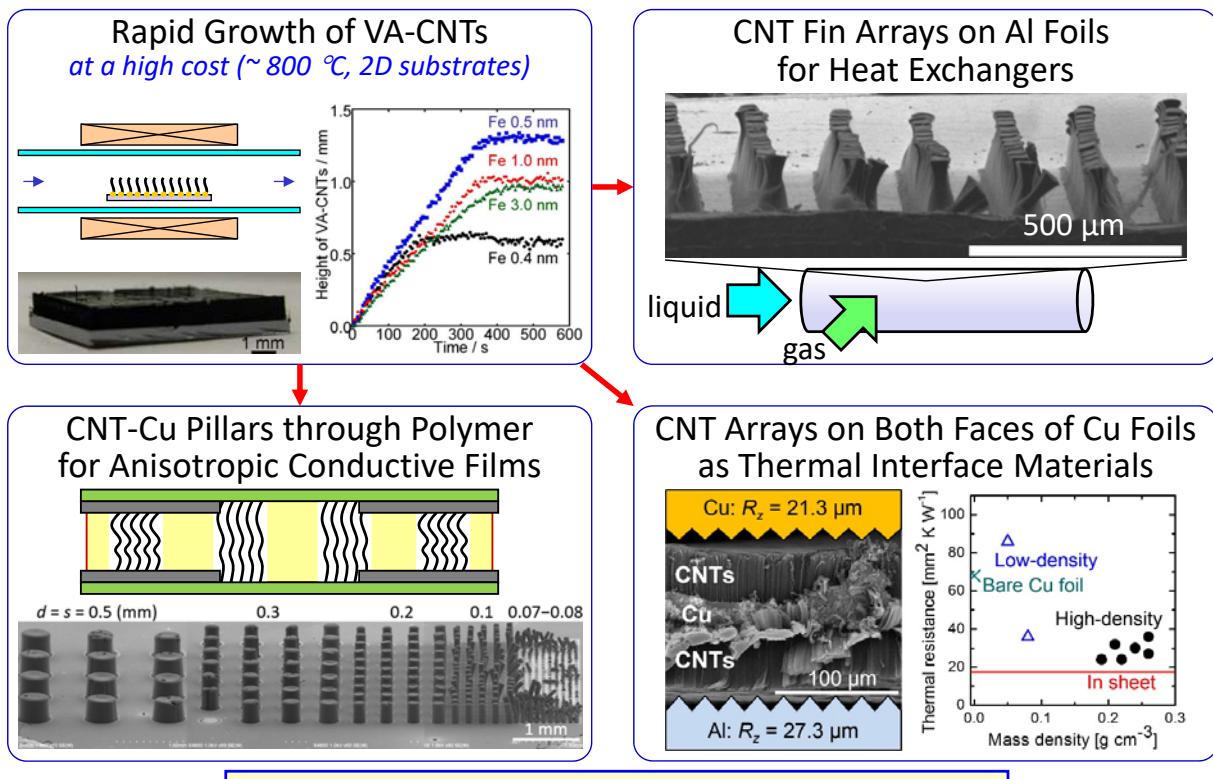
K. Sekiguchi, et al., Carbon 50, 2110 (2012).

Combinatorial Emitter Fabrication & Evaluation



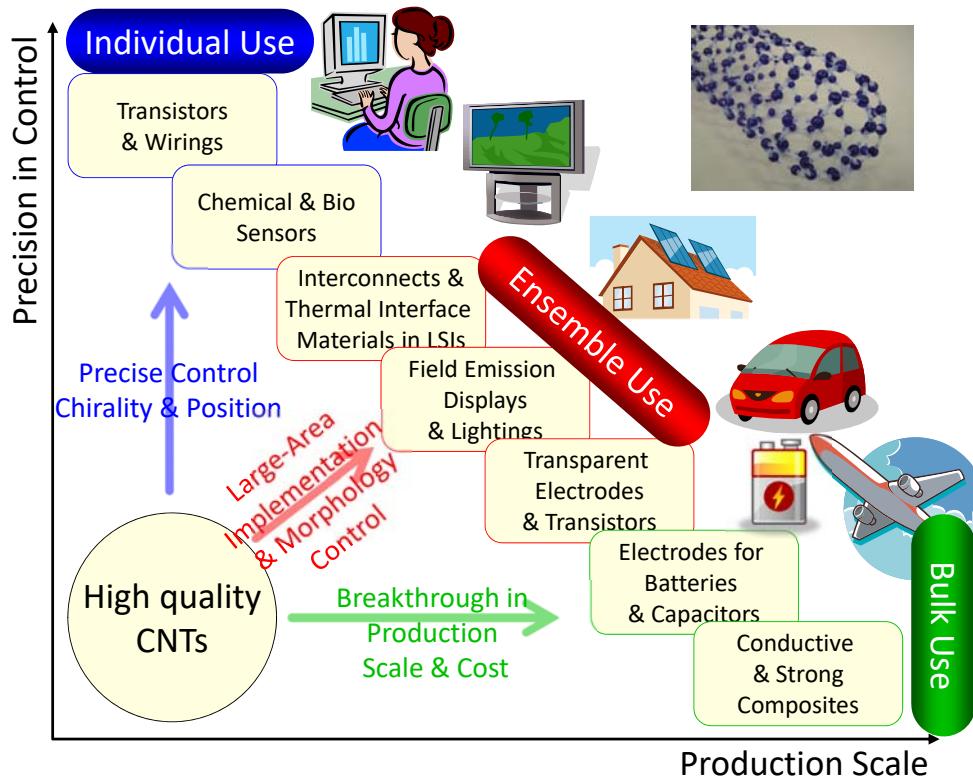
CNT growth is the easiest among various processes for emitter fabrication.
Easy implementation → Easy use for various purposes

Why CNTs Grow? → How to Grow CNTs?



Customize CVD process to each application target.

Opportunities & Production Challenges



Customizing CNT production processes to make dreams come true.

まとめ

先端材料の合成法は必ずしも合理的ではない。如何に合理的なプロセスを産み出す？

